

Quad Operational Amplifier

GENERAL DESCRIPTION

The XR-4212 is an array of four independent internally compensated operational amplifiers on a single silicon chip, each similar to the popular 741, but with a power consumption less than one 741. Good thermal tracking and matched gain-bandwidth products make these Quad Op-amps useful for active filter applications.

FEATURES

- Same Pinout as MC3403 and LM324
- Low Power Consumption—50 mW typ. and 120mW max.
- Short-Circuit Protection
- Internal Frequency Compensation
- No Latch-Up
- Wide Common-Mode and Differential Voltage Ranges
- Matched Gain-Bandwidth

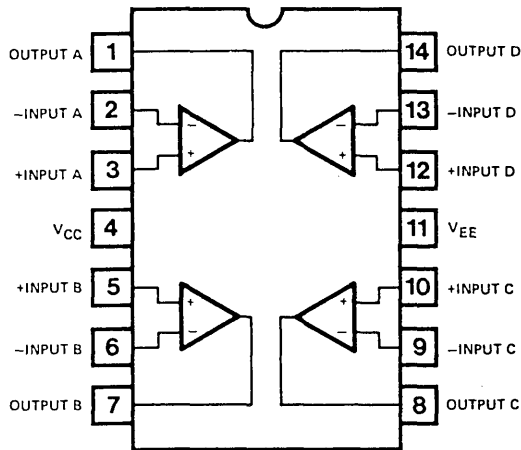
APPLICATIONS

- Buffer Amplifiers
- Summing/Differencing Amplifiers
- Instrumentation Amplifiers
- Active Filters
- Signal Processing
- Sample and Differencing
- I to V Converters
- Integrators
- Simulated Components
- Analog Computers

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	
XR-4212M	± 22V
XR-4212C	± 18V
Common Mode Voltage	V_{EE} to V_{CC}
Output Short-Circuit Duration	Indefinite
Differential Input Voltage	± 30V
Internal Power Dissipation	
Ceramic Package:	750 mW
Derate above $T_A = +25^\circ\text{C}$	6 mW/ $^\circ\text{C}$
Plastic Package:	625 mW
Derate above $T_A = +25^\circ\text{C}$	5 mW/ $^\circ\text{C}$
Storage Temperature Range:	-65°C to +150°C

FUNCTIONAL BLOCK DIAGRAM



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ORDERING INFORMATION

Part Number	Package	Operating Temperature
XR-4212M	Ceramic	-55°C to +125°C
XR-4212CN	Ceramic	0°C to +70°C
XR-4212CP	Plastic	0°C to +70°C

SYSTEM DESCRIPTION

The XR-4212 is a quad operational amplifier featuring improved performance over industry standard devices such as the 741.

XR-4212

ELECTRICAL CHARACTERISTICS

Test Conditions: $T_A = +25^\circ\text{C}$, $V_S = \pm 15\text{V}$, unless otherwise specified.

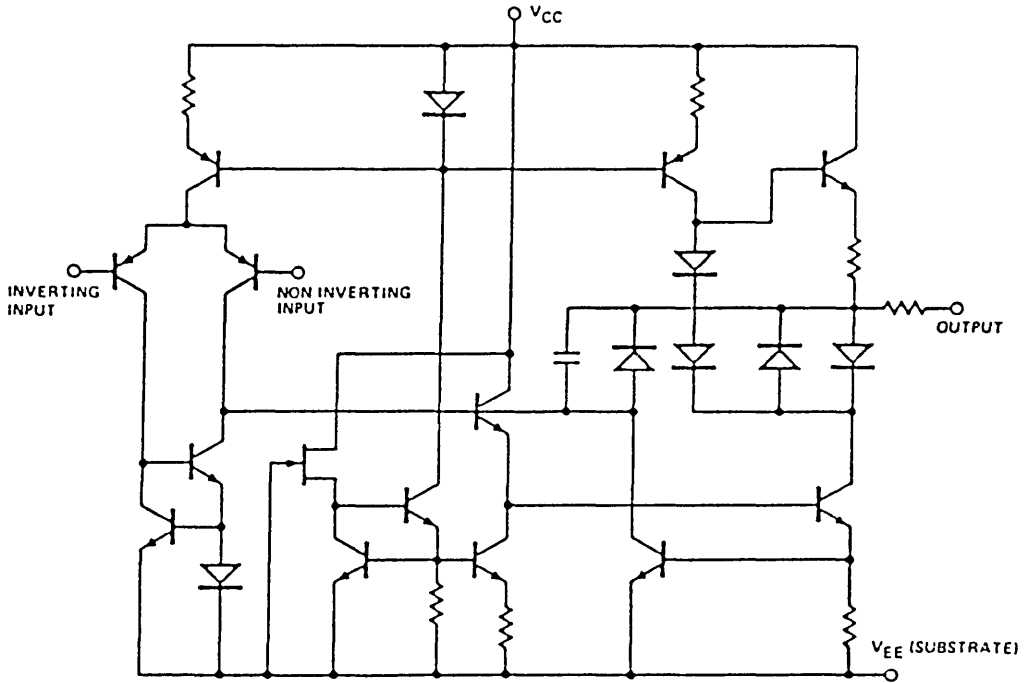
PARAMETERS	XR-4212M			XR-4212C			UNITS	SYMBOLS	CONDITIONS
	MIN	TYP	MAX	MIN	TYP	MAX			
Input Offset Voltage		1	5.0		1	6.0	mV	$ V_{io} $	$R_S \leq 10\text{K}\Omega$
Input Offset Current		10	50		10	50	nA	$ I_{io} $	
Input Bias Current		80	500		80	500	nA	$ I_b $	
Input Resistance	0.3	1.8		0.3	1.8		M Ω	R_{in}	
Large Signal Voltage Gain	20	60		5	40		V/mV	A_{VOL}	$R_L \geq 2\text{K}\Omega$ $V_{out} = \pm 10\text{V}$
Output Voltage Swing	± 12	± 14		± 12	± 14		V	V_{out}	$R_L \geq 10\text{K}\Omega$
	± 10	± 12		± 10	± 12		V	V_{out}	$R_L \geq 2\text{K}\Omega$
Input Voltage Range	± 12	± 13.5		± 12	± 13.5		V	V_{iCM}	
Common Mode Rejection Ratio	70	105		70	105		dB	CMRR	$R_S \leq 10\text{K}\Omega$
Supply Voltage Rejection Ratio		10	150		10	150	$\mu\text{V/V}$	PSRR	$R_S \leq 10\text{K}\Omega$
Power Consumption		50	120		50	120	mW	P_i	
Transient Response (unity gain)									
	Risetime	0.07			0.07		μs	t_r	$V_{in} = 20\text{mV}$ $R_L = 2\text{K}\Omega$ $C_L \leq 100\text{pF}$
Overshoot	20			20		%	t_o		
Unity Gain Bandwidth	2.0	3.0			3.0		MHz	BW	
Slew Rate (unity gain)		1.6			1.6		V/ μs	dV_{out}/dt	$R_L \geq 2\text{K}\Omega$
Channel Separation (open loop)		120			120		dB		$f = 10\text{KHz}$ $R_S = 1\text{K}\Omega$
	(Gain of 100)		105		105		dB		$f = 10\text{KHz}$ $R_S = 1\text{K}\Omega$
The following specifications apply for $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$ for XR-4212M: $0^\circ\text{C} \leq T_A \leq +70^\circ\text{C}$ for XR-4212C									
Input Offset Voltage			6.0			7.5	mV	$ V_{io} $	$R_S \leq 10\text{K}\Omega$
Input Offset Current			200			200	nA	$ I_{io} $	
Input Bias Current			1500			800	nA	I_b	
Large-Signal Voltage Gain	20			5			V/mV	A_{VOL}	$R_L \geq 2\text{K}\Omega$ $V_{out} = \pm 10\text{V}$
Output Voltage Swing	± 10			± 10			V	V_{out}	$R_L \geq 2\text{K}\Omega$
Power Consumption			150			150	mW	P_i	$V_S = \pm 15\text{V}$ $T_A = \text{High}$
			200			200	mW	P_i	$T_A = \text{Low}$
Output Short-Circuit Current	5	17	35	5	17	35	mA	I_{SC}	

TYPICAL PARAMETER MATCHING:

Test Conditions: $T_A = +25^\circ\text{C}$, $V_S = \pm 15\text{V}$ unless otherwise noted

PARAMETERS	XR-4212M		XR-4212C		UNITS	SYMBOLS	CONDITIONS
	TYP	TYP	TYP	TYP			
Input Offset Voltage	± 1.0		± 2.0		mV	$ V_{io} $	$R_S \geq 10\text{K}\Omega$
Input Offset Current	± 7.5		± 7.5		nA	$ I_{io} $	
Input Bias Current	± 15		± 15		nA	I_b	
Voltage Gain	± 0.5		± 1.0		dB	A_{VOL}	$R_S \geq 2\text{K}\Omega$

XR-4212



1/4 of XR-4212

EQUIVALENT SCHEMATIC DIAGRAM

Dual Low Noise Operational Amplifier

GENERAL DESCRIPTION

The XR-4560 is a dual low noise, wide bandwidth operational amplifier ideal for active filter applications. The device is similar to the XR-1458/4558, with greatly enhanced slew rate, bandwidth, and guaranteed noise characteristics.

Pin for pin compatibility allows direct substitution for industry standard dual op amps where the low noise and wide bandwidth of the XR-4560 is imperative.

FEATURES

- High Gain, Low Input Noise
- Internally Compensated
- Wide Small Signal Bandwidth
- Interchangeable with General Purpose Dual Op Amps

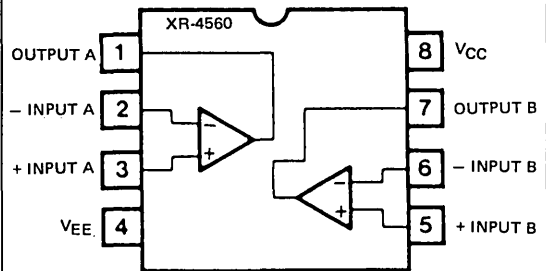
APPLICATIONS

- High Gain, Low Noise Amplifier
- High Performance Active Filter
- Small Signal Amplifier
- Servo Control System
- Telephone Channel Amplifier

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±18 V
Power Dissipation	500 mW
Derate Above at 25°C	5 mW/°C
Operating Temperature	0°C to +70°C
Storage Temperature	-55°C to +125°C
Differential Input Voltage	±30 V
Common Mode Range	VEE to VCC

FUNCTIONAL BLOCK DIAGRAM



ORDERING INFORMATION

Part Number	Package	Operating Temperature
XR-4560CP	Plastic	0°C to 70°C
XR-4560CN	Ceramic	0°C to 70°C
XR-4560MD	SO-8	0°C to 70°C

SYSTEM DESCRIPTION

The XR-4560 dual op amp offers guaranteed low noise and a 10 MHz small signal bandwidth. Slew rate typically exceeds 4 V/μs. Internal protection circuitry includes latch-up elimination, short circuit current limiting, and internal compensation.

The two amplifiers are completely independent, sharing only power supply connections.

XR-4560

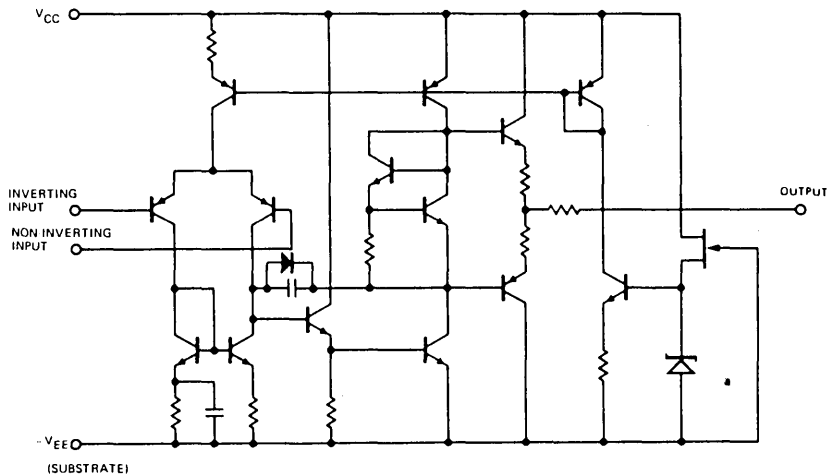
ELECTRICAL CHARACTERISTICS

Test Conditions: $T_A = 25^\circ\text{C}$, $V_{CC} = +15\text{ V}$, $V_{EE} = -15\text{ V}$, unless specified otherwise.

SYMBOL	PARAMETERS	MIN.	TYP.	MAX.	UNIT	CONDITIONS
V_{OS}	Input Offset Voltage		0.5	6.0	mV	$R_S \leq 10\text{K}\Omega$
I_{OS}	Input Offset Current		5	200	nA	
I_B	Input Bias Current		50	500	nA	
R_{in}	Input Resistance		5		$M\Omega$	
A_V	Open Loop Gain	86	100		dB	$R_L \geq 2\text{K}\Omega$
	Output Voltage Swing	± 12 ± 10	± 14 ± 13		V V	$R_L \geq 10\text{K}\Omega$ $R_L \geq 2\text{K}\Omega$
V_{ICM}	Common Mode Range	± 12	± 14		V	
CMRR	Common Mode Rejection Ratio	70	90		dB	$R_S \leq 10\text{K}\Omega$
PSRR	Supply Voltage Rejection Ratio		30	150	$\mu\text{V/V}$	$R_S \leq 10\text{K}\Omega$
S_R	Slew Rate		4.0		$\text{V}/\mu\text{s}$	$A_V = 1$, $R_L \geq 2\text{K}\Omega$
BW	Unity Gain Bandwidth		10		MHz	$A_V = 1$
P_i	Power Consumption		50		mW	$R_L = \infty$
	Channel Separation		100		dB	$A_V = 100$
e_n	Input Noise Voltage			2.2	μV	$f = 10\text{ Hz to } 30\text{ kHz}$ Circuit of Figure 7

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EQUIVALENT SCHEMATIC DIAGRAM



(One Channel Only)

TYPICAL CHARACTERISTICS

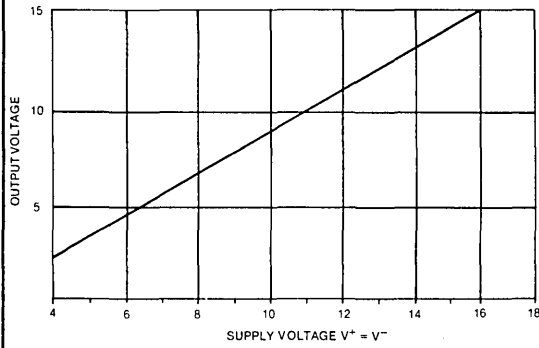


Figure 1. Output Voltage Swing vs Supply Voltage

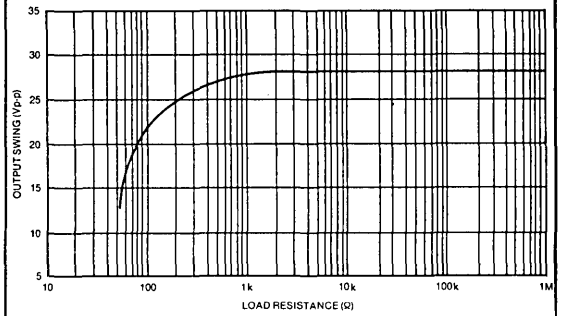


Figure 2. Loaded Output Voltage Swing

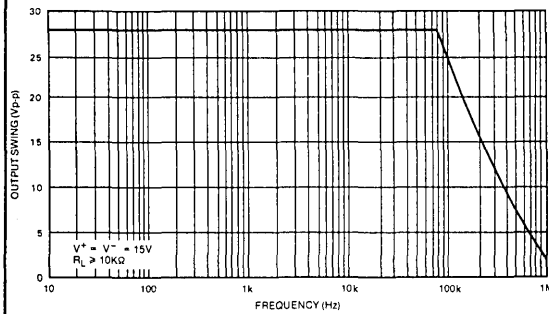


Figure 3. Large Signal Frequency Response

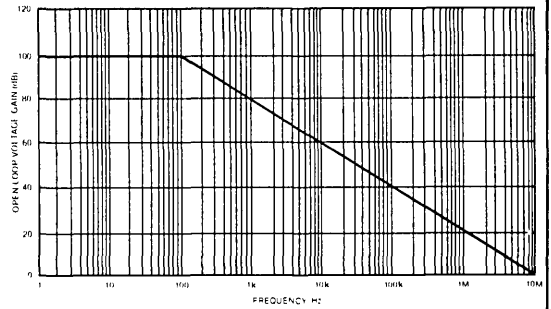


Figure 4. Open Loop Gain

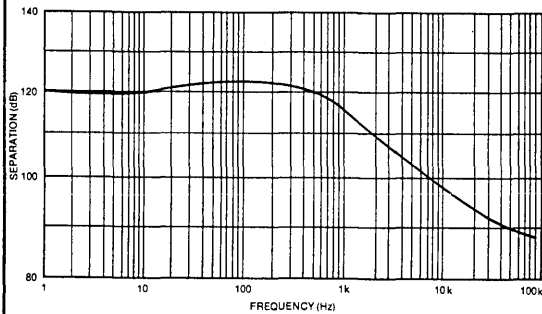


Figure 5. Channel Separation vs Frequency

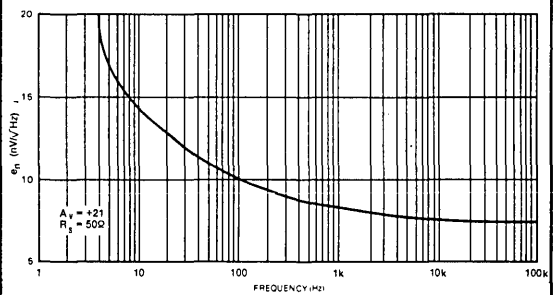


Figure 6. Input Noise Voltage Spectral Density

Noise measurements made on a Quantek 2173-2181 noise analyzer with the XR-4560 in a standard noninverting circuit with $A_V = 21$.

XR-4560

TYPICAL APPLICATIONS

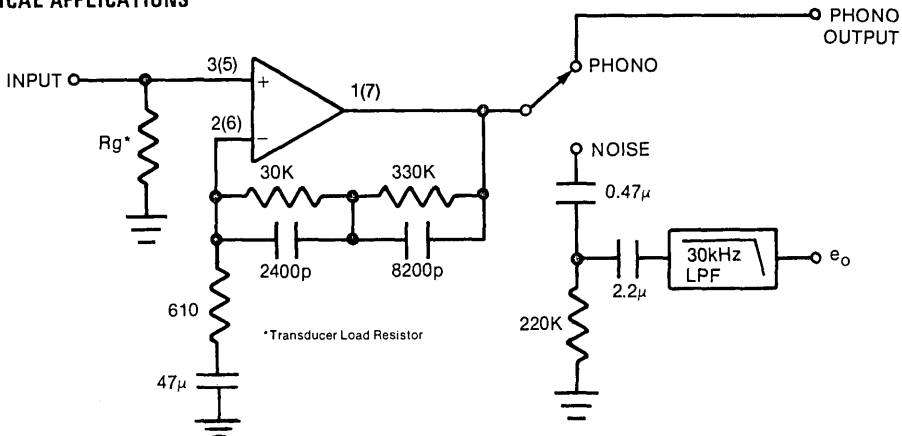


Figure 7. RIAA Equalized Phonograph Preamplifier (One Channel) & Broadcast Noise Test Circuit

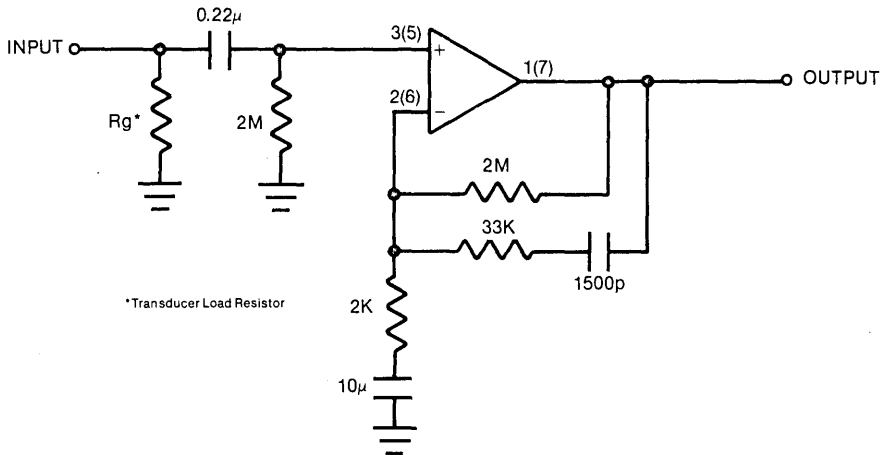


Figure 8. NAB Equalized Tape Playback Preamplifier (One Channel)

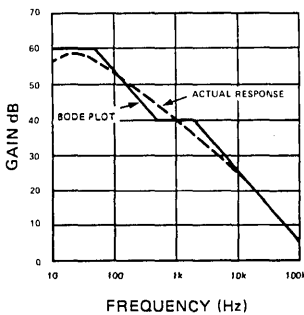


Figure 9. RIAA-Type Phonograph Equalization

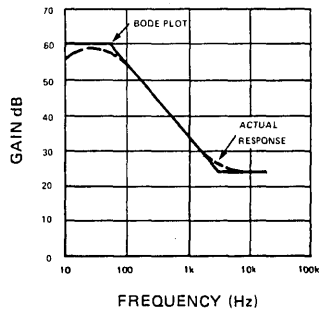


Figure 10. NAB-Type Tape Player Equalization